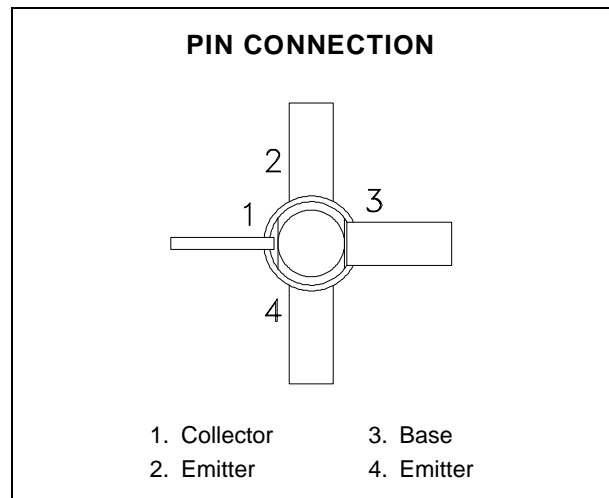
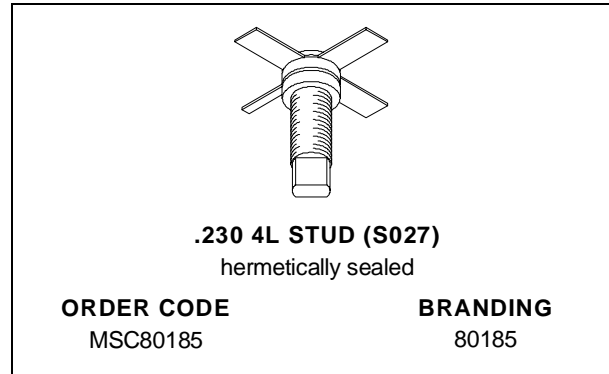


**RF & MICROWAVE TRANSISTORS  
GENERAL PURPOSE LINEAR APPLICATIONS**

- EMITTER BALLASTED
- CLASS A LINEAR OPERATION
- COMMON EMITTER
- VSWR CAPABILITY 20:1 @ RATED CONDITIONS
- ft 3.2 GHz TYPICAL
- NOISE FIGURE 12.0 dB @ 2 GHz
- P<sub>OUT</sub> = 28 dBm MIN. @ 2.0 GHz



**DESCRIPTION**

The MSC80185 is a hermetically sealed NPN power transistor featuring a unique matrix structure. This device is specifically designed for Class A linear applications to provide high gain and high output power at the 1.0 dB compression point.

**ABSOLUTE MAXIMUM RATINGS** (T<sub>case</sub> = 25°C)

Symbol	Parameter	Value	Unit
P <sub>DISS</sub>	Power Dissipation (see Safe Area)	—	W
I <sub>C</sub>	Device Bias Current	300	mA
V <sub>CE</sub>	Collector-Emitter Bias Voltage*	20	V
T <sub>J</sub>	Junction Temperature	200	°C
T <sub>STG</sub>	Storage Temperature	- 65 to +200	°C

**THERMAL DATA**

R <sub>TH(j-c)</sub>	Junction-Case Thermal Resistance*	35	°C/W
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\*Applies only to rated RF amplifier operation

## MSC80185

### ELECTRICAL SPECIFICATIONS ( $T_{\text{case}} = 25^{\circ}\text{C}$ )

#### STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
$BV_{\text{CBO}}$	$I_{\text{C}} = 1\text{mA}$	$I_{\text{E}} = 0\text{mA}$	50	—	—	V
$BV_{\text{EBO}}$	$I_{\text{E}} = 1\text{mA}$	$I_{\text{C}} = 0\text{mA}$	3.5	—	—	V
$BV_{\text{CEO}}$	$I_{\text{C}} = 5\text{mA}$	$I_{\text{B}} = 0\text{mA}$	20	—	—	V
$I_{\text{CEO}}$	$V_{\text{CE}} = 18\text{V}$		—	—	0.5	mA
$h_{\text{FE}}$	$V_{\text{CE}} = 5\text{V}$	$I_{\text{C}} = 100\text{mA}$	15	—	120	—

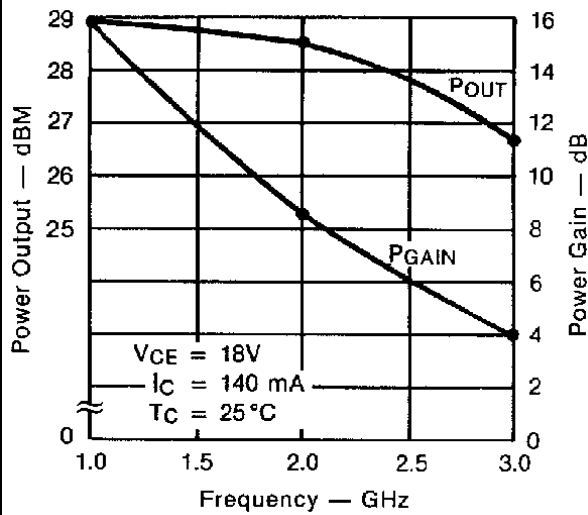
#### DYNAMIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
$G_{\text{P}}^*$	$f = 2.0\text{ GHz}$	$P_{\text{OUT}} = 28\text{ dBm}$	7.5	8.5	—	dB
$\Delta G_{\text{P}}^*$	$f = 2.0\text{ GHz}$	$P_{\text{OUT}} = 28\text{ dBm}$	—	—	1	dB
$C_{\text{OB}}$	$f = 1\text{ MHz}$	$V_{\text{CB}} = 28\text{ V}$	—	—	3.0	pF

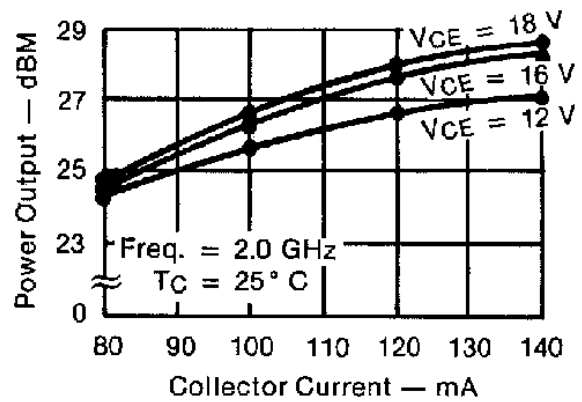
\* Note:  $V_{\text{CE}} = 18\text{V}$   
 $I_{\text{C}} = 140\text{mA}$

TYPICAL PERFORMANCE

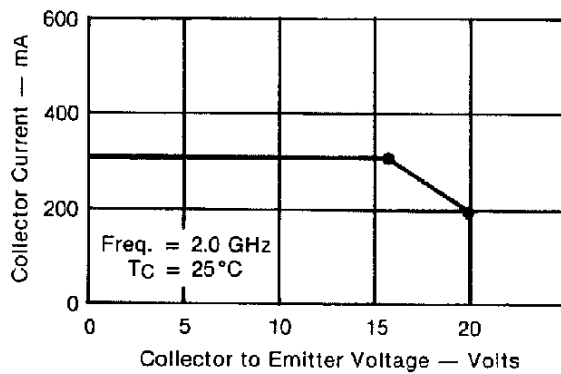
TYPICAL POWER OUTPUT & GAIN @ 1dB COMPRESSION POINT vs FREQUENCY



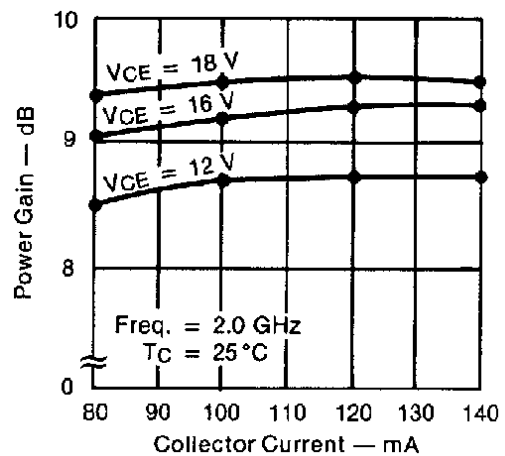
TYPICAL POWER OUTPUT & GAIN @ 1dB COMPRESSION POINT vs COLLECTOR CURRENT



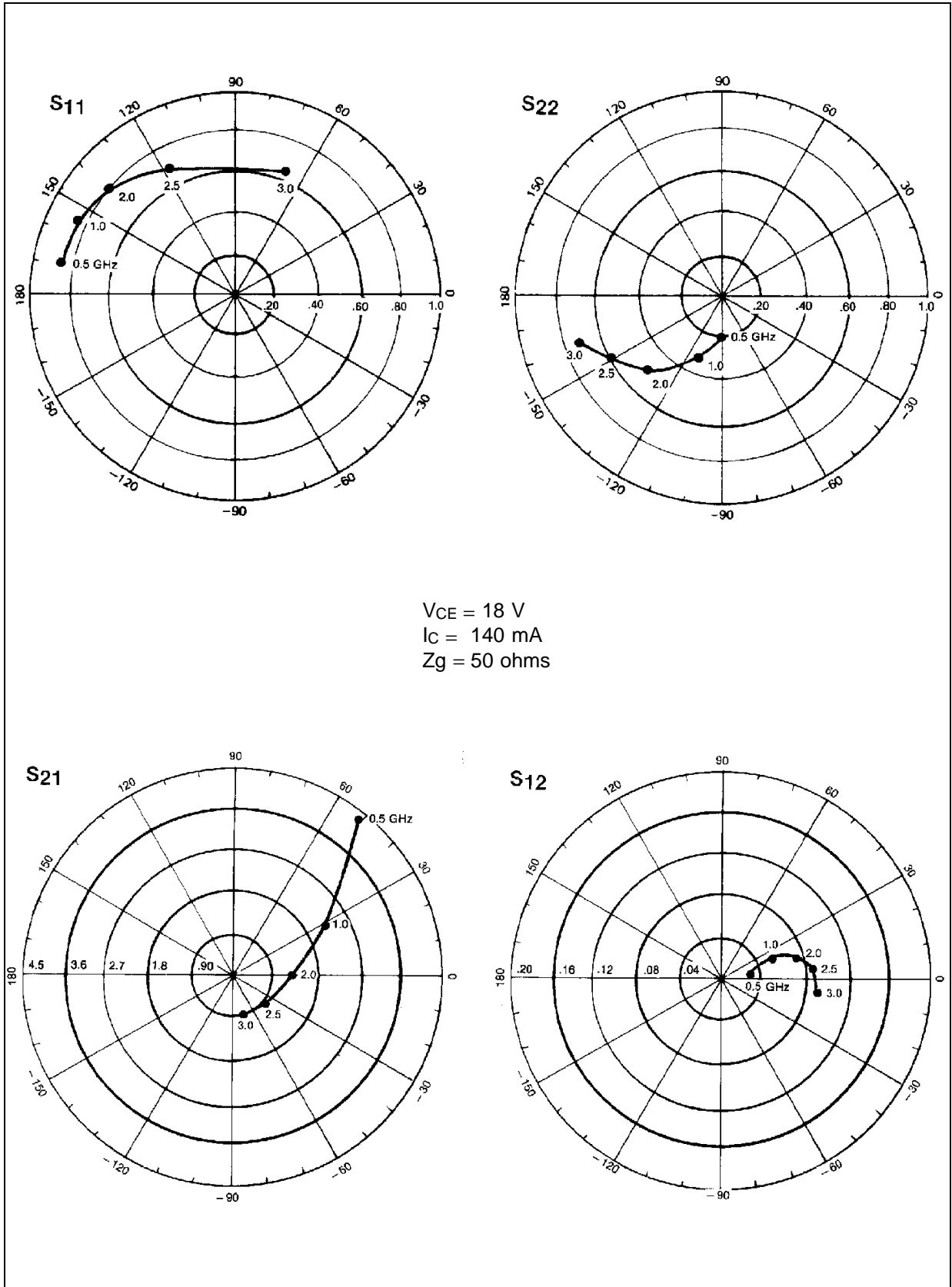
MAXIMUM OPERATING AREA FOR FORWARD BIAS OPERATION



TYPICAL LINEAR GAIN vs COLLECTOR CURRENT



TYPICAL S-PARAMETERS





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